

TITLE OF THE INVENTION

Machine suitable for plating a cavity of a semi-conductive or conductive substrate such as a through via structure

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ABSTRACT

The invention relates to a machine (1) adapted to metallise a cavity of a semi-conductive or conductive substrate such as a structure of the through silicon via type, according to a metallisation process comprising the steps consisting of:

10 a) depositing an insulating dielectric layer in the cavity,
b) depositing a barrier layer to diffusion of the filling metal,
c) filling the cavity by electrodeposition of metal, preferably copper, and
d) carrying out annealing of the substrate,

15 characterised in that it comprises a series of wet-processing modules (10-60) configured to conduct steps a), b) and c) by wet-processing in a chemical bath (B) and at least one additional module (70) adapted to conduct annealing step d) of the substrate (S) such that the machine (1) is capable of executing the entire metallisation process of the cavity.

20 Figure 1